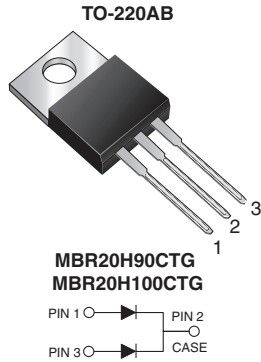




KERSEMI

MBR20H90CTG & MBR20H100CTG

High Barrier Technology for Improved High Temperature Performance



FEATURES

- Guardring for overvoltage protection
- Lower power losses, high efficiency
- Low forward voltage drop
- Low leakage current
- High forward surge capability
- High frequency operation
- Solder dip 260 °C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

TYPICAL APPLICATIONS

For use in high frequency rectifier of switching mode power supplies, freewheeling diodes, dc-to-dc converters or polarity protection application.

MECHANICAL DATA

Case: TO-220AB

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test, HE3 suffix for high reliability grade (AEC Q101 qualified), meets JESD 201 class 2 whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	10 A x 2
V_{RRM}	90 V, 100 V
I_{FSM}	150 A
V_F	0.70 V
I_R	3.5 μ A
T_J max.	175 °C

MAXIMUM RATINGS ($T_C = 25$ °C unless otherwise noted)				
PARAMETER	SYMBOL	MBR20H90CTG	MBR20H100CTG	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	90	100	V
Working peak reverse voltage	V_{RWM}	90	100	V
Maximum DC blocking voltage	V_{DC}	90	100	V
Maximum average forward rectified current at $T_C = 155$ °C total device per diode	$I_{F(AV)}$	20 10		A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	150		A
Peak repetitive reverse current per diode at $t_p = 2$ μ s, 1 kHz	I_{RRM}	0.5		A
Voltage rate of change (rated V_R)	dV/dt	10 000		V/ μ s
Operating junction and storage temperature range	T_J, T_{STG}	- 65 to + 175		°C

ELECTRICAL CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Maximum instantaneous forward voltage per diode ⁽¹⁾	$I_F = 10\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	V_F	0.80	0.85	V
	$I_F = 10\text{ A}$	$T_J = 125\text{ }^\circ\text{C}$		0.64	0.70	
	$I_F = 20\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$		0.87	0.93	
	$I_F = 20\text{ A}$	$T_J = 125\text{ }^\circ\text{C}$		0.74	0.80	
Maximum reverse current per diode at working peak reverse voltage ⁽¹⁾		$T_J = 25\text{ }^\circ\text{C}$ $T_J = 125\text{ }^\circ\text{C}$	I_R	- -	3.5 4.5	μA mA

Note:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

THERMAL CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted)			
PARAMETER	SYMBOL	MBR	UNIT
Typical thermal resistance per diode	$R_{\theta JC}$	2.0	$^\circ\text{C/W}$

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (G)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	MBR20H100CTG-E3/45	1.85	45	50/tube	Tube
TO-220AB	MBR20H100CTGHE3/45 ⁽¹⁾	1.85	45	50/tube	Tube

Note:

(1) Automotive grade AEC Q101 qualified

RATINGS AND CHARACTERISTICS CURVES

($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

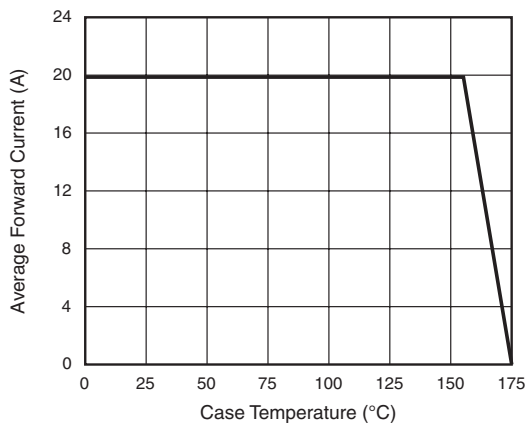


Figure 1. Forward Derating Curve

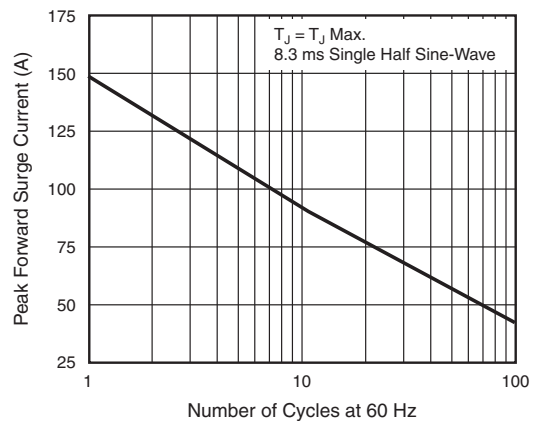


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

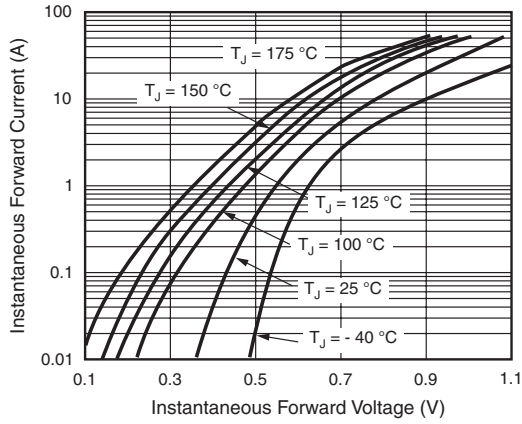


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

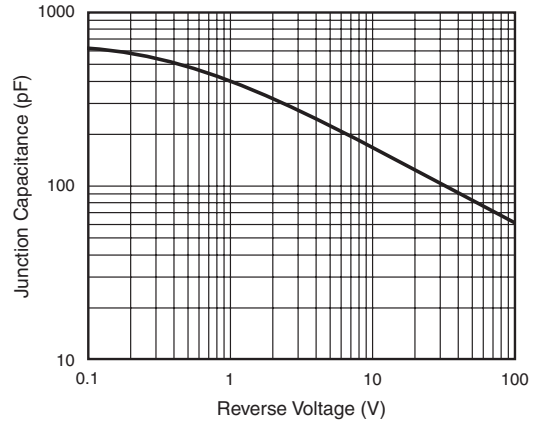


Figure 5. Typical Junction Capacitance Per Diode

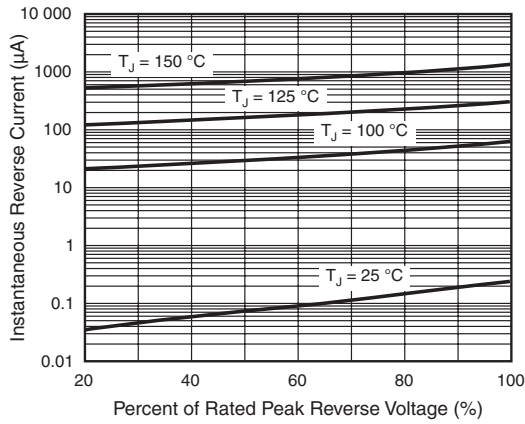


Figure 4. Typical Reverse Characteristics Per Diode

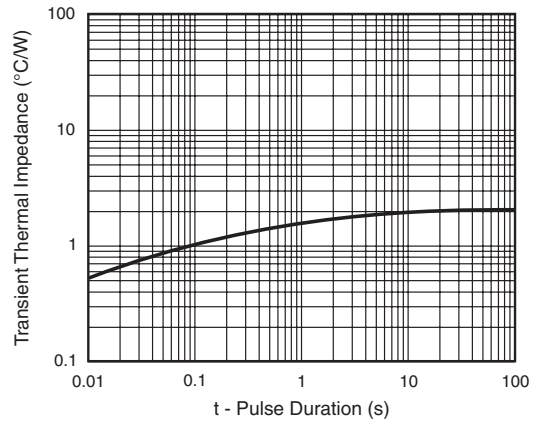


Figure 6. Typical Transient Thermal Impedance Per Diode

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

TO-220AB

